NSN 5962-01-357-6616

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View Online at https://aerobasegroup.com/nsn/5962-01-357-6616

view Offilite at https://aerobasegroup.com/hsi//0302-01-0010
Body Length:
1.060 inches
Body Width:
Between 0.220 inches and 0.310 inches
Body Height:
Between 0.130 inches and 0.185 inches
Maximum Power Dissipation Rating:
2.0 watts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
Features Provided:
Bidirectional and bipolar and programmable and high impedance and w/clock and w/disable and monolithic
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Transistor-transistor logic
Input Circuit Pattern:
16 input
Case Outline Source And Designator:
D-8 mil-m-38510
Current Rating Per Characteristic:
180.00 milliamperes reverse current, dc absolute
Product Name:
And/or invert gate array
Voltage Rating And Type Per Characteristic:
-0.5 volts power source and 12.0 volts power source
Time Rating Per Chacteristic:
30.00 nanoseconds propagation delay time, high to low level output and 30.00 nanoseconds propagation delay time, low to high level
output
Memory Device Type:
Pal
Test Data Document:
96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And Quantity:
20 printed circuit
Shelf Life:
N/a

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Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

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